

[Name of Document] Specification

[Title] Alkaline etching solution for semiconductor wafer and alkaline etching method

5 [Field of the Invention]

[0001]

The present invention relates to a field of semiconductor-wafer manufacturing technology and, in particular, to a novel alkaline etching solution for silicon wafer, an alkaline etching method using the solution, a silicon-wafer manufacturing method using the solution, and further a silicon wafer obtained through the method.

[Background]

[0002]

15 When a silicon wafer for use in integrated circuits, such as ICs and LSIs, and discrete semiconductor elements, such as transistors and diodes, a monocrystal obtained through a Czochralski method (CZ method) or a floating-zone method (FZ method) is cut off by using an inner-diameter-blade cutter or a wire saw for beveling of sidelines and, after a lap process (lapping) is performed for improving the flatness on a main surface with free abrasive grains, wet etching is performed for removing a process distortion applied to the wafer through the above-mentioned processes and then mirror polishing is performed. Such wet etching includes acid etching using a mixed

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acid of, for example, hydrofluoric acid, nitric acid, and acetic acid, and alkaline etching using alkali, such as sodium hydroxide or potassium hydroxide.

[0003]

5 While acid etching has an advantage capable of controlling an etching rate and the state of the surface of the wafer after etching, there are drawbacks of a large etching rate to cause deterioration in flatness of the wafer improved through a lapping process.

10 On the other hand, although the etching rate is slow, alkaline etching has an advantage of capable of keeping the flatness of the wafer improved through a lapping process, thereby achieving a wafer with the excellent flatness after etching. In recent years, to allow finer microfabrication, an
15 extremely high-level flatness has been demanded for semiconductor wafers. For this reason, this alkaline etching
C has been widely used.

[0004]

 In the alkaline etching technology that has been used so
20 far, an alkaline component with a concentration smaller than 48 to 50 weight percent in an alkaline etching solution has widely been used.

[0005]

 However, such an alkaline etching solution widely used
25 in general has anisotropy in which an etching speed on a (100)

surface and an etching speed on a (111) surface are different from each other approximately sixty to one hundred times. This poses a problem in which a concave portion (hereinafter referred to as a "facet") occurs on the surface of the wafer, and
5 asperities remain on the surface of the wafer after etching. If such asperities on the surface of the wafer are large (if the surface roughness is large), this poses problems of the occurrence of particles in the device manufacturing process and a decrease in productivity in a polishing process.

10 [0006]

To address such problems, a technology disclosed in, for example, Japanese Patent Laid-Open Publication No. 2003-229392 has been suggested, in which a alkaline solution with a high concentration (equal to or larger than 50 weight percent) is
15 used to control the etching speed and lessen the influence of anisotropy, thereby decreasing the size of the facet to improve the surface roughness. However, the alkaline solution with a high concentration may be frozen in winter, thereby posing a problem in view of convenience.

20 [0007]

Then, there has been strong demand for the alkaline etching solution for silicon wafers which is capable of improving the surface roughness of wafers without using the alkaline solution with high concentration.

25 [Disclosure of the invention]

[Problem to be solved]

[0008]

5 An object of the present invention is to provide a silicon wafer etching method using an alkaline etching solution capable of improving a surface roughness even with a relatively low alkaline concentration that has been conventionally widely used.

10 [0009]

 The inventors have diligently studied in order to develop an excellent alkaline etching solution that satisfies the demands described above and, as a result, have found that, by using a bromate-added alkaline etching solution as a caustic
15 alkaline aqueous solution generally used, the size of a facet occurring on the surface of a silicon wafer can be reduced.

[0010]

 Also, the inventors have found that effects of bromate
20 obtained from the findings in alkaline etching can be kept by adding nitrate.

[0011]

 That is, the present invention relates to an alkaline etching solution in which an alkaline aqueous solution contains
25 bromate.

[0012]

Further, the present invention relates to an alkaline etching solution in which an alkaline aqueous solution contains bromate and nitrate.

5 [0013]

Still further, the present invention relates to the alkaline etching solution, wherein the bromate is sodium bromate.

[0014]

10 Still further, the present invention relates to the alkaline etching solution, wherein the nitrate is sodium nitrate.

[0015]

Still further, the present invention relates to a method
15 of etching a silicon wafer with an alkaline solution, wherein the alkaline solution is a caustic alkaline aqueous solution containing bromate.

[0016]

Still further, the present invention relates to a method
20 of etching a silicon wafer with an alkaline solution, wherein the alkaline solution is a caustic alkaline aqueous solution containing bromate and nitrate.

[0017]

Still further, the present invention relates to the
25 silicon-wafer etching method, wherein the bromate is sodium

bromate.

[0018]

Still further, the present invention relates to the silicon-wafer etching method, wherein the nitrate is sodium
5 nitrate.

[0019]

Still further, the present invention relates to a method of manufacturing a semiconductor silicon wafer, comprising the step of performing alkaline etching by using a caustic alkaline
10 aqueous solution containing bromate, wherein a wafer after the etching has a surface roughness Ra equal to or smaller than 0.27 μm .

[0020]

Still further, the present invention relates to a method
15 of manufacturing a semiconductor silicon wafer, comprising the step of performing alkaline etching by using a caustic alkaline aqueous solution with bromate added thereto, wherein a wafer after the etching has a surface roughness Ra equal to or smaller than 0.27 μm .

20 [Effect of the invention]

[0021]

By using the alkaline etching solution (solution containing bromate), the size of the facet can be significantly reduced and the surface roughness of the wafer can be improved
25 without significant decrease in etching speed, compared with

the case of using a caustic alkaline aqueous solution conventionally used in general. Also, the surface roughness can be sufficiently improved without a high-concentration alkaline aqueous solution. Therefore, alkaline etching can be conveniently performed. Furthermore, by using an alkaline etching solution (solution containing bromate and nitrate), bromate consumption is suppressed in the course of alkaline etching, thereby keeping the above-described effects. Thus, it is possible to perform alkaline etching capable of obtaining a wafer with improved surface roughness in an extremely economical manner with a low environmental load.

[Best embodiment for carrying out the invention]

[0022]

(Silicon wafer)

15

A silicon wafer capable of being etched by applying the etching solution of the present invention is not particularly restrictive. The etching solution usable in the present invention can be applied to various silicon wafers conventionally known to the art.

Specifically, there are no limitations in size (diameter and thickness), the presence or absence of doping with various elements, or the presence or absence of pre-process.

20

[0023]

(Alkaline etching solution)

25

The alkaline etching solution usable in the present invention has a feature in which a conventionally known alkaline etching solution for silicon wafer contains a small amount

alkaline etching solution for silicon wafer contains a small amount of bromate. Here, the alkaline etching solution means an aqueous solution containing an alkaline component as an etching component and, if required, other components.

5 [0024]

Here, the alkaline etching solution usable in the present invention is not particularly restrictive as long as it is a conventionally-known alkaline etching solution for silicon wafer including ones commercially available. The alkaline etching solution can be selected appropriately in view of a desired etching characteristic and characteristics of a semiconductor wafer to be etched. As an alkaline component, an inorganic alkali hydroxide is preferable. In particular, sodium hydroxide, potassium hydroxide, and lithium hydroxide, and a mixture thereof are preferable. In the present invention, the use of sodium hydroxide is particularly preferable.

[0025]

Also, the concentration of the alkaline component is not particularly restrictive and can be selected appropriately according to etching conditions and others. A general range of concentration of the alkaline component is 20 to 60 weight percent and, preferably, 45 to 50 weight percent. Here, the concentration of the alkaline component represents a weight percent of alkaline hydroxide in the aqueous solution. If the concentration is lower than the above range, it is difficult

to control the etching speed and suppress a facet on the surface.
A concentration higher than the above range is not preferable
because of posing problems such as insolubility of bromate in
a high-concentration alkaline aqueous solution and freeze of
5 the alkaline aqueous solution itself.

[0026]

Furthermore, the purity of the alkaline component usable
in the present invention is not particularly restrictive and
can be selected appropriately in consideration of the degree
10 of metallic contamination associated with etching. When using
in a semiconductor manufacturing process, a
commercially-available solution with high purity can be used
as it is. Also, if required, the solution is preferably
formulated from an alkaline component with a low concentration
15 of metallic impurities contained therein and ultrapure water.

[0027]

Still further, since the concentration of the alkaline
component varies according to the etching, it is preferable to
measure the concentration appropriately at the time of use or
20 the like, and re-supply an etching solution or water as required.
A measurement can be performed by using, for example,
neutralization titration. Still further, although normal
storage conditions will suffice, an environment that can
prevent the occurrence of alkaline carbonate, which will cause
25 a change in concentration and affect etching, is preferable.

[0028]

5 The alkaline etching solution usable in the present invention has a feature of containing bromate. Here, the bromate is not particularly restrictive, and can include sodium bromate, potassium bromate, and lithium bromate. In particular, sodium salt is preferable. As the bromate, the one commercially available can be used as it is or after purification.

[0029]

10 The concentration of the bromate is not particularly restrictive. A preferable range is 0.01 to 10 weight percent, more preferably, 0.1 to 3.0 weight percent, and still more preferably, 0.1 to 1.0 weight percent. If the concentration is too low, a sufficient improvement in surface roughness cannot
15 be obtained. Also, a concentration higher than the above range is not preferable in view of cost and possible mixture of impurities from the bromate.

[0030]

A method of adding the bromate is not particularly
20 restrictive. The bromate can be solved in advance before use for storage and can be used as it is for etching. Alternatively, the solution can be formulated at the time of use for etching. On the other hand, the inventors have found that, when a bromate-containing alkaline etching solution is used for
25 etching, as the number of times of etching is increased, the

effect of addition of the bromate is decreased. Since the alkaline etching solution may be used under different etching conditions or used for etching of silicon wafers of various shapes, it is preferable to calculate the dissolved amount of silicon in the etching solution that can be found from the amount of etching, in place of the number of times of etching.

Therefore, if the dissolved amount of silicon is increased and the effect is decreased, the etching solution may be replaced, or bromate may be further added for use.

[0031]

Another feature of the alkaline etching solution usable the present invention is that nitrate is added in addition to bromate. Effects of the nitrate are based on unexpected findings described below obtained by the inventors. That is, in an alkaline etching method using a bromate-added alkaline aqueous solution, the facet size is indeed excellently controlled and can be extremely decreased, thereby obtaining a silicon wafer with an improved surface roughness. However, if such an alkaline etching solution is repeatedly used, the above effects are decreased. However, when the alkaline etching solution with nitrate further added thereto is used, the above effects can be kept without reduction.

[0032]

The nitrate to be added for this purpose is not particularly restrictive, and can include sodium nitrate,

potassium nitrate, and lithium nitrate with high purity. In the present invention, sodium nitrate is preferable. As the nitrate, the one commercially available can be used as it is or after purification.

5 [0033]

The concentration of the nitrate is not particularly restrictive. A preferable range for use to achieve the effects is 0.01 to 10.0 weight percent. In particular, the nitrate is preferably equimolecular to or more than the bromate. By adding
10 the nitrate equimolecular to or more than the bromate being added, the above effects can be kept for the longer time even when the alkaline etching solution is used repeatedly.

[0034]

A method of adding the nitrate is not particularly
15 restrictive. The nitrate can be added to the alkaline aqueous solution irrespectively of the order of addition of the bromate. Also, the nitrate can be solved in advance before use for storage and can be used as it is for etching. Alternatively, the solution can be formulated at the time of use for etching.

20 [0035]

(Alkaline etching method)

The alkaline etching method according to the present invention has a feature of using any of the above alkaline etching solution and, in particular, the method is for
25 (semiconductor) silicon wafer.

[0036]

Etching conditions for use in the alkaline etching method according to the present invention are not particularly restrictive. Conditions that are set when a
5 conventionally-known alkaline etching solution is used are preferable and, according to the type of a semiconductor wafer to be etched (size, thickness, crystal orientation), any etching amount, etching speed, etching time, temperature, agitation, and others can be selected appropriately.

10 [0037]

Furthermore, an etching apparatus usable for the alkaline etching method according to the present invention is not particularly restrictive. An apparatus used when a conventionally-known alkaline etching solution is used is
15 preferable and, according to the type of a semiconductor wafer to be etched and the etching conditions, any apparatus can be selected appropriately. Specifically, for example, an etching bath having a circulating system, such as a circulating pump, a filter, and a heater, is usable.

20 [0038]

The etching method using the alkaline etching solution (solution containing bromate) according to the present invention is excellent in that a silicon wafer with an improved surface roughness can be obtained. On the other hand, only with
25 bromate, the effects are decreasing as etching is repeated.

Therefore, the degree of repeated use is preferably determined by performing etching using an appropriate standard test sample and measuring surface roughness of a silicon wafer obtained with respect to the dissolved amount of silicon in the etching
5 solution for comparison.

[0039]

Also, the etching method using the alkaline etching solution (containing bromate and nitrate) suppresses a decrease in the effects of the bromate in accordance with repetition of
10 etching, and therefore can be used repeatedly. Also in this case, the degree of such repeated use is preferably determined by performing etching using an appropriate standard test sample and measuring surface roughness of a silicon wafer obtained with respect to the dissolved amount of silicon in the etching
15 solution for comparison.

[0040]

(Semiconductor-silicon-wafer manufacturing method)

The may be used to present invention to manufacture a
20 semiconductor silicon wafer.

[0041]

The semiconductor silicon wafer manufactured through the
25 manufacturing method according to the present invention is

particularly excellent in surface roughness. The surface roughness can be evaluated through various measuring schemes according to various purposes. In particular, such an evaluation can be made from the surface roughness and/or surface glossiness measured through various measuring means conventionally known. Specific measuring apparatuses and methods include Surftest SJ-201P from Mitsutoyo Corporation for surface roughness and a glossmeter PG-1M from Nippon Denshoku Industries, Co., Ltd., for surface glossiness.

10 [0042]

Furthermore, the purpose of visually evaluating the shape of facet can be fulfilled by observing the shape of the surface. Specifically, a surface observation by a microscope is a preferable evaluation method. With this, for example, the shape, size, and depth of the facet can be evaluated.

[0043]

The present invention is described in more detail below with reference to the examples, but is not restricted to these examples.

20 [Example]

[0044]

In examples and comparative examples described below, the following evaluation method was used.

"Wafer evaluation test scheme"

25 (1) Etching speed (etching rate: $\mu\text{m}/\text{sec}$) : Ultragate 9700

from ADE was used to measure the thickness of the center of a wafer before and after etching, and an etching speed was calculated based on the following equation:

Etching speed: (Thickness before etching-Thickness after
5 etching)/etching time.

(2) Wafer surface roughness: Surftest SJ-201P from Mitsutoyo Corporation was used to measure Ra based on JIS B0601-1994.

(3) Wafer surface glossiness: A glossmeter PG-1M from
10 Nippon Denshoku Industries, Co., Ltd. was used to measure the glossiness based on JIS Z8741/K5400 with a lighting/light-receiving angle of 60 degrees.

(4) Etching surface observation: A surface-shape measurement microscope VF-7500 from Keyence Corporation was
15 used for wafer surface observation after etching (magnification: 100x).

[0045]

[Example 1] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 0 g/L)

20 In a caustic alkaline aqueous solution of 65 L of 48 weight percent of sodium hydroxide (48% of CLEARCUT-S from Tsurumi Soda Co., Ltd.), 196 g of sodium bromate (from Wako Pure Chemical Industries, Ltd., a Wako reagent chemicals) and 111 g of sodium nitrate (from Wako Pure Chemical Industries, Ltd., reagent
25 chemicals) were dissolved to formulate an alkaline aqueous

solution containing 0.20 weight percent of sodium bromate and 0.11 weight percent of sodium nitrate as an alkaline etching solution. With the formulated alkaline etching solution, a block-type etching bath with a filling capacity of 65 liters was filled. In the filling bath, twenty silicon wafers having a diameter of eight inches subjected to both-side lapping were soaked as being loaded on a carrier. With these wafers being rotated in the aqueous solution together with the carrier (20 rpm), etching was performed for approximately 25 μm on both sides for approximately seven minutes at a liquid temperature of 90 degrees Celsius. Then, the wafers were moved to a water washing bath for cleaning and drying. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon. Furthermore, a microphotograph of the surface of a resultant wafer was shot and shown in Fig. 2.

[0046]

[Example 2] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 0.3 g/L)

Etching similar to that of Example 1 was repeatedly performed without replacing the etching solution after the

process of Example 1, thereby using an alkaline aqueous solution with the dissolved amount of silicon of 0.3 g/L as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

10 [0047]

[Example 3] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 0.6 g/L)

In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 0.6 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0048]

[Example 4] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 0.9

g/L)

In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 0.9 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0049]

[Example 5] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 1.2 g/L)

In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 1.2 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0050]

[Example 6] (alkaline etching solution containing sodium

bromate and sodium nitrate, dissolved amount of silicon: 1.5 g/L)

In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 1.5 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0051]

[Example 7] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 1.8 g/L)

In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 1.8 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0052]

[Example 8] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 2.1 g/L)

In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 2.1 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0053]

[Example 9] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 2.4 g/L)

In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 2.4 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0054]

[Example 10] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon: 2.7 g/L)

5 In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 2.7 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the
10 resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0055]

15 [Example 11] (alkaline etching solution containing sodium bromate and sodium nitrate, dissolved amount of silicon:
3.0 g/L)

 In a manner similar to that of Example 2, an alkaline aqueous solution with its silicon concentration of 3.0 g/L was
20 used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in
25 Fig. 1, the surface roughness of the resultant wafers is plotted

with respect to the dissolved amount of silicon. Furthermore, a microphotograph of the surface of a resultant wafer was shot and shown in Fig. 3.

[0056]

- 5 [Example 12] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 0 g/L)

An alkaline aqueous solution was formulated in a manner similar to Example 1 except that sodium nitrate was not added, and used as the etching solution. Furthermore, silicon wafers
10 were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant
15 wafers is plotted with respect to the dissolved amount of silicon. Furthermore, a microphotograph of the surface of a resultant wafer was shot and shown in Fig. 4.

[0057]

- [Example 13] (alkaline etching solution containing sodium
20 bromate, dissolved amount of silicon: 0.3 g/L)

Etching similar to that of Example 1 was repeatedly performed without replacing the etching solution after the process of Example 12, thereby using an alkaline aqueous solution with the dissolved amount of silicon of 0.3 g/L as the
25 etching solution. Silicon wafers were etched in a manner

similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0058]

[Example 14] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 0.6 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with its silicon concentration of 0.6 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0059]

[Comparative Example 1] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 0.9 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with its silicon concentration of 0.9 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed,

wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted
5 with respect to the dissolved amount of silicon.

[0060]

[Comparative Example 2] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 1.2 g/L)

In a manner similar to that of Example 13, an alkaline
10 aqueous solution with its silicon concentration of 1.2 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described
15 testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0061]

[Comparative Example 3] (alkaline etching solution containing
20 sodium bromate, dissolved amount of silicon: 1.5 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with its silicon concentration of 1.5 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed,
25 wafer surface roughness, and wafer surface glossiness of the

resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

5 [0062]

[Comparative Example 4] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 1.8 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with its silicon concentration of 1.8 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0063]

[Comparative Example 5] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 2.1 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with the dissolved amount of silicon of 2.1 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the

above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

5 [0064]

[Comparative Example 6] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 2.4 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with its silicon concentration of 2.4 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0065]

[Comparative Example 7] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 2.7 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with its silicon concentration of 2.7 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described

testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon.

[0066]

- 5 [Comparative Example 8] (alkaline etching solution containing sodium bromate, dissolved amount of silicon: 3.0 g/L)

In a manner similar to that of Example 13, an alkaline aqueous solution with its silicon concentration of 3.0 g/L was used as the etching solution. Silicon wafers were etched in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon. Furthermore, microphotograph of the surface of a resultant wafer was shot and shown in Fig. 5.

[0067]

[Comparative Example 9] (48% sodium hydroxide aqueous solution)

- 20 An alkaline aqueous solution was formulated in a manner similar to Example 1 except that neither sodium bromate nor sodium nitrate was added, and used as the etching solution. In a manner similar to those of Examples 1 to 11, alkaline aqueous solutions each with the dissolved amount of silicon (g/L) being
- 25 0, 0.3, 0.6, 0.9, 1.2, 1.5, 1.8, 2.1, 2.4, 2.7, 3.0 were used

as the etching solutions to etch silicon wafers in a manner similar to that of Example 1. Then, the etching speed, wafer surface roughness, and wafer surface glossiness of the resultant wafers were measured through the above-described testing method. The results are shown in Table 1. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon. Also, in Fig. 1, the surface roughness of the resultant wafers is plotted with respect to the dissolved amount of silicon. Furthermore, microphotographs of the surfaces of the resultant wafers obtained by using the etching solutions with silicon amounts of dissolution of 0 g/L and 3.0 g/L were shot and shown in Figs. 6 and 7, respectively.

[0068]

Table 1

Evaluation	Dissolved amount of silicon in etching solution [g/L]	Etching speed [$\mu\text{m}/\text{sec}$]	Surface roughness Ra [μm]	Glossiness
Example 1	0	0.059	0.25	91.7
Example 2	0.3	0.060	0.25	80.5
Example 3	0.6	0.058	0.24	89.1
Example 4	0.9	0.060	0.24	88.8
Example 5	1.2	0.058	0.25	85.7
Example 6	1.5	0.059	0.26	87.6
Example 7	1.8	0.060	0.23	90.5
Example 8	2.1	0.059	0.25	91.1
Example 9	2.4	0.059	0.23	86.7
Example 10	2.7	0.060	0.25	88.8
Example 11	3.0	0.059	0.25	97.7
Example 12	0	0.059	0.26	89.9
Example 13	0.3	0.059	0.24	89.7
Example 14	0.6	0.061	0.29	110.2
Comparative Example 1	0.9	0.063	0.34	111.1

Comparative Example 2	1.2	0.064	0.32	118.6
Comparative Example 3	1.5	0.064	0.34	119.3
Comparative Example 4	1.8	0.062	0.34	119.2
Comparative Example 5	2.1	0.064	0.33	118.4
Comparative Example 6	2.4	0.063	0.33	118.9
Comparative Example 7	2.7	0.064	0.34	121.1
Comparative Example 8	3.0	0.064	0.36	117.4
Comparative Example 9	0	0.062	0.34	120.5
	0.3	0.064	0.32	121.5
	0.6	0.063	0.33	120.3
	0.9	0.065	0.33	119.7
	1.2	0.064	0.35	122.1
	1.5	0.063	0.31	122.6
	1.8	0.063	0.33	123.9
	2.1	0.064	0.32	123.6
	2.4	0.064	0.32	124.5
	2.7	0.062	0.34	124.1
	3.0	0.064	0.32	123.8

[0069]

From Table 1 and Fig. 1, in alkaline etching using an alkaline etching solution containing sodium bromate and sodium nitrate (Examples 1 to 11) and an alkaline etching solution containing sodium bromate (Examples 12 to 14), it is apparent that the surface roughness can be significantly improved compared with alkaline etching using a 48% sodium hydroxide aqueous solution containing neither sodium bromate nor sodium nitrate as an alkaline etching solution (Comparative Example 9). Furthermore, in the alkaline etching solution containing sodium bromate and sodium nitrate (Examples 4 to 11), in comparison with the alkaline etching solution containing sodium

bromate (Comparative Examples 1 to 8), it can be seen that, even when the dissolved amount of silicon in the etching solution is increased due to repeated use, the effects can be kept and a silicon wafer with an improved surface roughness can be
5 achieved.

Also, in comparison with Figs. 2 to 4 and Figs. 5 to 7, the size of a facet can be significantly reduced by using the alkaline etching solution according to the present invention.

[BRIEF DESCRIPTION OF THE DRAWINGS]

10 [0070]

Fig. 1 shows a graph depicting the results of Examples 1 to 14 and Comparative Examples 1 to 9. The horizontal axis represents dissolved amount of silicon (g/L) and the vertical axis represents a surface roughness (μm) of a wafer obtained.
15 The hollow circles represent alkaline etching solution containing sodium bromate and sodium nitrate (Examples 1 to 11), the crosses represent alkaline etching solution containing sodium bromate (Examples 12 to 14 and Comparative Examples 1 to 8), and black circles represent alkaline etching solution
20 of 48% NaOH (Comparative Example 9);

Fig. 2 shows a micrograph (magnification: 100 $\times$) of a wafer surface obtained through Example 1;

Fig. 3 shows a micrograph (magnification: 100 $\times$) of a wafer surface obtained through Example 11;

25 Fig. 4 shows a micrograph (magnification: 100 $\times$) of a

wafer surface obtained through Example 12;

Fig. 5 shows a micrograph (magnification: 100×) of a wafer surface obtained through Comparative Example 8;

Fig. 6 shows a micrograph (magnification: 100×) of a
5 wafer surface obtained through Comparative Example 9 (dissolved
amount of silicon: 0 g/L); and

Fig. 7 shows a micrograph (magnification: 100×) of a
wafer surface obtained Comparative Example 9 (dissolved amount
of silicon: 3.0 g/L).

Claims:

1. A silicon-wafer etching method using an alkaline solution,
wherein the alkaline solution is an alkaline aqueous solution
5 comprising bromate and nitrate.
2. The silicon-wafer etching method according to claim 1, wherein
the alkaline solution comprises an alkali hydroxide in a
concentration of 20 - 60 % by weight.
10
3. The silicon-wafer etching method according to claim 2, wherein
the alkaline solution comprises an alkali hydroxide in a
concentration of 45 - 50 % by weight.
- 15 4. The silicon-wafer etching method according to any one of claims
1 to 3, wherein the bromate is sodium bromate.
5. The silicon-wafer etching method according to any one of claims
1 to 4, wherein the nitrate is sodium nitrate.
20
6. The silicon-wafer etching method according to any one of claims
1 to 5, wherein a wafer after the etching has a surface roughness
Ra equal to or smaller than 0.27 μm .
- 25 7. The silicon-wafer etching method according to any one of claims
1 to 6, wherein the concentration of the bromate is 0.01 to 10 %
by weight.
8. The silicon-wafer etching method according to any one of claims
30 1 to 7, wherein the concentration of the nitrate is 0.01 to 10 %
by weight.